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The invention relates to the semiconductor production technology, in particular to processes for obtaining porous semiconductor structures.

The process for obtaining porous semiconductor structures consists in that onto the semiconductor's surface it is deposited a mask, onto the uncovered regions there are implanted high-energy ions, then the mask is removed, and the semiconductor surface is subjected to the electrochemical pickling. Novelty consists in that prior to pickling there is repeatedly deposited a mask mainly onto the regions which have been implanted with ions, onto the uncovered regions there are implanted ions of high-energy different from the previous one and it is removed the mask.

Claims: 1